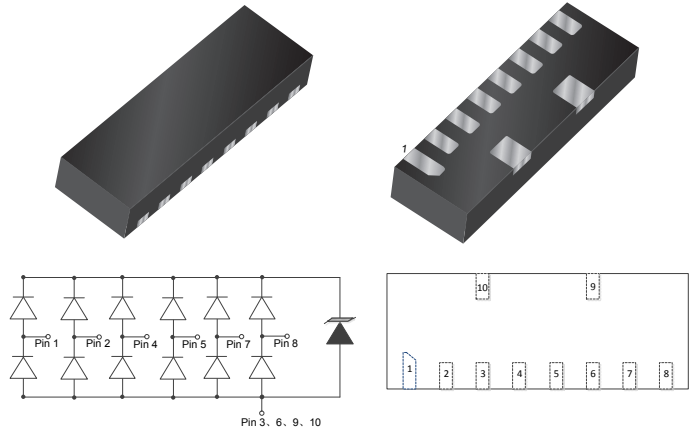


Ultra Low Capacitance ESD/TVS Array in DFN3310

Features

- 30Watts peak pulse power ($t_p = 8/20\mu s$)
- DFN 3310 Package
- Protect up to 6-lines
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (0.2pF typical I/O to I/O)
- ESD Protection for high-speed data lines to:
 - IEC 61000-4-2 $\pm 8kV$ contact $\pm 15kV$ air
 - IEC 61000-4-4 (EFT) 40A (5/50ns)
 - IEC 61000-4-5 (Lightning) 3A (8/20 μs)



Mechanical Data

- **Case:** DFN3310 (plastic package).
Lead free;RoHS compliant;Halogen free
- **Molding Compound Flammability Rating:**
UL 94 V-0
- **Terminals:** High temperature soldering guaranteed:
260 °C/10 sec. at terminals

Applications

- USB 3.0/3.1, Type C
- HDMI 1.4/2.0, Display Port 1.3
- Unified Display interface
- Digital visual interface
- Microcontroller Input Protection

Absolute Maximum Ratings

Ratings at 25 °C, ambient temperature unless otherwise specified

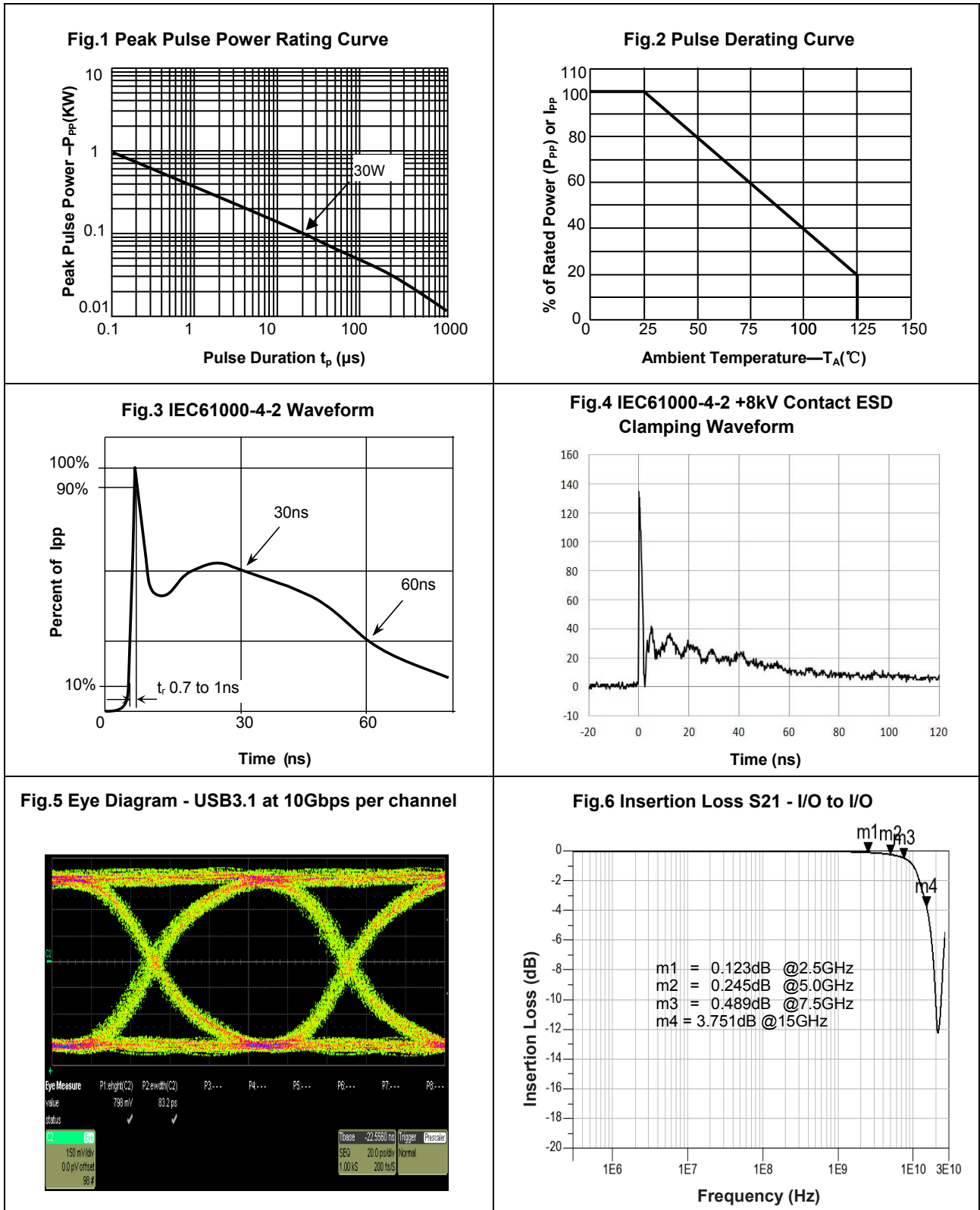
Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_P=8/20\mu S$)	P_{PP}	30	W
ESD contact/air discharge (IEC-61000-4-2)	V_{ESD}	8/15	kV
Peak Pulse Current ($t_P = 8/20\mu S$)	I_{PP}	3	A
Junction Temperature	T_J	-55 to +125	°C
Storage temperature	T_{STG}	-55 to +150	°C

Electrical Characteristics

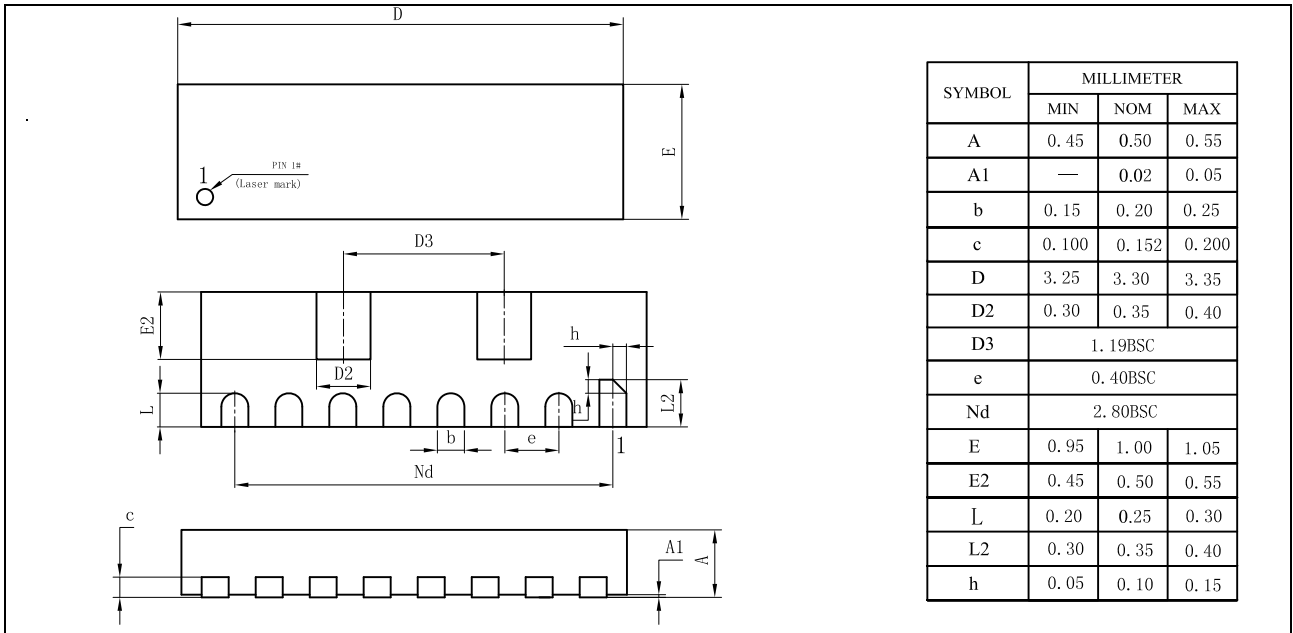
($T_A = 25\text{ °C}$ unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Reverse stand-off Voltage	V_{RWM}				5	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	6	7.2	9.5	V
Reverse Leakage Current	I_R	$V_R=5V$		0.1	0.5	μA
Clamping Voltage(SURGE)	V_C	$I_{PP}=3A, T_P=8/20\mu S$		10		V
Junction Capacitance	C_J	$V_R=0V, f=1MHz, I/O$ to I/O		0.2		pF
	C_J	$V_R=0V, f=1MHz, I/O$ to GND		0.4		pF

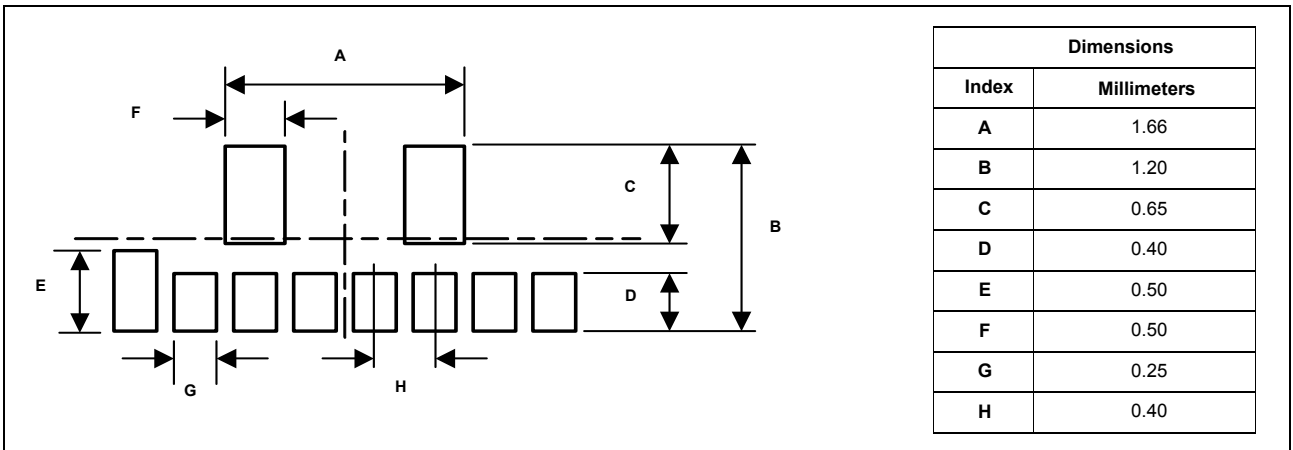
Typical Characteristics (T_{amb} = 25 °C unless otherwise specified)



Package Dimensions



PAD Dimensions



Ordering information

Order code	Marking	Package	Packaging option	Base quantity	Packaging specification
TESD3310UC5VU	L5U	DFN3310	Tape and reel	3000pcs / reel	EIA STD RS-481